Product Preview

Hex Buffer

The MC74LVX50 is an advanced high speed CMOS buffer fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: tpD = 5.0ns (Typ) at $V_{CC} = 3.3$ V
- Low Power Dissipation: $I_{CC} = 4\mu A$ (Max) at $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Low Noise: $V_{OLP} = 0.5V$ (Max)
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V

A1 1 2 Y1 A2 3 4 Y2 A3 5 6 Y3 Y = 1 A4 9 8 Y4 A5 11 10 Y5 A6 13 12 Y6

A1 — 1 — Y1 A2 — 1 — Y2 A3 — 1 — Y3 A4 — 1 — Y4 A5 — 1 — Y5 A6 — 1 — Y6

LOGIC SYMBOL

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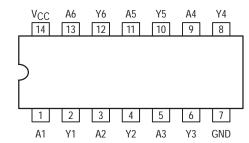


14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G



14-LEAD SOIC EIAJ M SUFFIX CASE 965

PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping
MC74LVX50D	SOIC	55 Units/Rail
MC74LVX50DT	TSSOP	96 Units/Rail
MC74LVX50M	SOIC EIAJ	50 Units/Rail

FUNCTION TABLE

A Input	Y Output
L	L
H	H

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	Vcc	-0.5 to +7.0	V
DC Input Voltage	VIN	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	Vout	-0.5 to 7.0 -0.5 to V _{CC} + 0.5	V
Input Diode Current	lik	-20	mA
Output Diode Current (VOUT < GND; VOUT > VCC)	lok	+20	mA
DC Output Current, per Pin	lout	+25	mA
DC Supply Current, V _{CC} and GND	Icc	+50	mA
Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	P _D	500 450	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	VCC	2.0	3.6	V
DC Input Voltage	VIN	0.0	5.5	V
DC Output Voltage	Vout	0.0	Vcc	V
Operating Temperature Range	TA	- 55	+85	°C
Input Rise and Fall Time V _{CC} = 3.3V ± 0.3V	t _r , t _f	0	100	ns/V

[†]Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS

			VCC	1	A = 25°0	2	$T_A \le 85^{\circ}C$ $T_A \le 125^{\circ}C$		125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High–Level Input Voltage		2.0 3.0 3.6	1.5 2.1 2.4			1.5 2.1 2.4		1.5 2.1 2.4		V
V _{IL}	Maximum Low–Level Input Voltage		2.0 3.0 3.6			0.5 0.9 0.8		0.5 0.9 0.8		0.5 0.9 0.8	V
VOH	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA I _{OH} = -50μA I _{OH} = -4mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0 4.5		1.9 2.9 2.48		1.9 2.9 2.34		V
VOL	Maximum Low-Level Output Voltage VIN = VIH or VIL	I _{OL} = 50μA I _{OL} = 50μA I _{OL} = 4mA	2.0 3.0 3.0		0.0 0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44		0.1 0.1 0.52	V
IN	Maximum Input Leakage Current	V _{IN} = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μА
ICC	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μА

AC ELECTRICAL CHARACTERISTICS (C_{load} = 50 pF, Input t_{f} = t_{f} = 3.0ns)

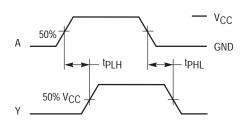
				T _A = 25°C		T _A ≤ 85°C		T _A ≤ 125°C			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
· · · · ·	Propogation Delay,	V _{CC} = 2.7V	C _L = 15 pF C _L = 50 pF		6.0 8.0	7.0 9.5		9.0 12.5		11.0 15.0	ns
	Input A to Y	V _{CC} = 3.3 ± 0.3V	$C_L = 15 pF$ $C_L = 50 pF$		5.0 7.5	5.5 8.0		7.0 10.5		9.0 13.0	
C _{IN}	Maximum Input Capacitance				4	10		10		10	pF

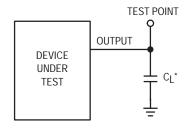
		Typical @ 25°C, V _{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 1.)	18	pF

^{1.} CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}$. CpD is used to determine the no–load dynamic power consumption; $P_{D} = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$, $C_L = 50 \text{pF}$, $V_{CC} = 5.0 \text{V}$)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
VOLP	Quiet Output Maximum Dynamic VOL	0.3	0.5	V
VOLV	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V
VIHD	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V





*Includes all probe and jig capacitance
Figure 2. Test Circuit

Figure 1. Switching Waveforms

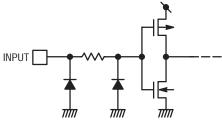
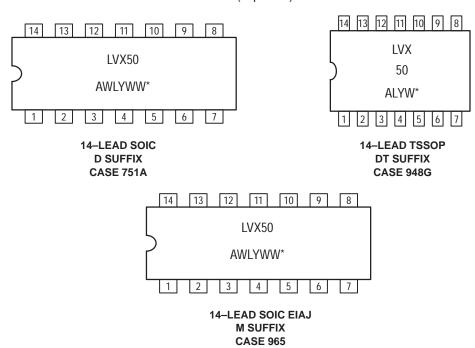


Figure 3. Input Equivalent Circuit

MARKING DIAGRAMS

(Top View)

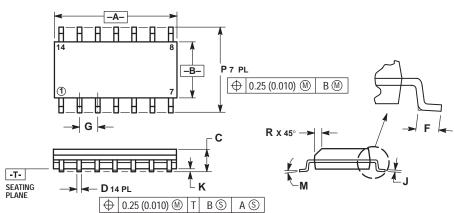


*See Applications Note #AND8004/D for date code and traceability information.

PACKAGE DIMENSIONS

D SUFFIX

PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



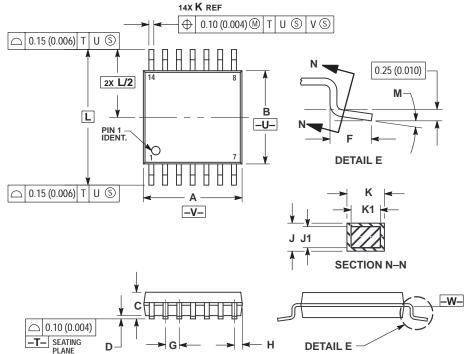
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948G-01 **ISSUE O**



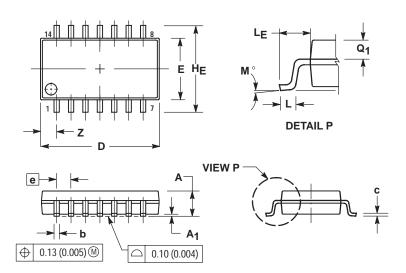
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH,
 PROTRUSIONS OR GATE BURRS. MOLD FLASH
 OR GATE BURRS SHALL NOT EXCEED 0.15
 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED
 OR (0.006) PER SIDE.
- 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. DIMENSION A AND B ARE TO BE DETERMINED
- AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

PACKAGE DIMENSIONS

M SUFFIX

PLASTIC SOIC EIAJ PACKAGE CASE 965-01 ISSUE O



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH
- MEASURED AT THE PARTING LINE. MOLD FLASH
 OR PROTRUSIONS SHALL NOT EXCEED 0.15
 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE 1.0 COATED ON THE 1.0 WER DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS IN		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
Α ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Ε	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LF	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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